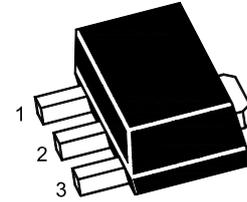


Plastic-Encapsulate Transistors

TRANSISTOR (PNP)

FEATURES

- High voltage
- High transition frequency
- Complementary to 2SC2881U



1.Base 2.Collector 3.Emitter
SOT-89 Plastic Package

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.8	A
P_C	Collector Power Dissipation	0.5	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	250	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-1\text{mA}, I_E=0$	-120			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10\text{mA}, I_B=0$	-120			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1\text{mA}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-120\text{V}, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-5\text{V}, I_C=-100\text{mA}$	80		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-500\text{mA}, I_B=-50\text{mA}$			-1	V
Base-emitter voltage	V_{BE}	$V_{CE}=-5\text{V}, I_C=-500\text{mA}$			-1	V
Transition frequency	f_T	$V_{CE}=-5\text{V}, I_C=-100\text{mA}$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$			30	pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	80-160	120-240
Marking	DO	DY

Typical Characteristics

